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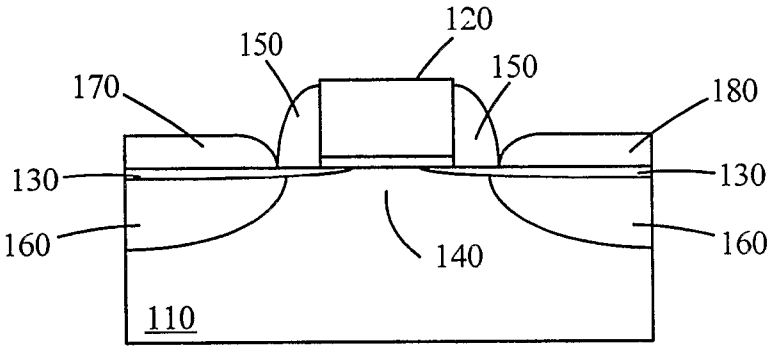
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(54) Title: STRAINED NMOS TRANSISTOR FEATURING DEEP CARBON DOPED REGIONS AND RAISED DONOR DOPED SOURCE AND DRAIN



(57) Abstract: Some embodiments of the present invention include providing carbon doped regions and raised source/drain regions to provide tensile stress in NMOS transistor channels.

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